

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MSESD8D3.3CAT5G

Product specification

Features

- 60Watts peak pulse power ($t_p = 8/20\mu s$)
- Tiny DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 $\pm 15kV$ contact $\pm 20kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 6A (8/20 μs)

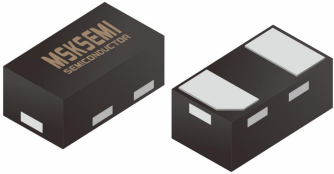
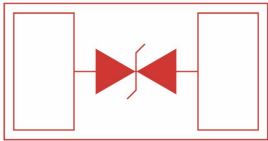

Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Data

- DFN1006 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Reference News

PACKAGE OUTLINE	Schematic & PIN Configuration	Marking
		
DFN1006		

Absolute Maximum Rating

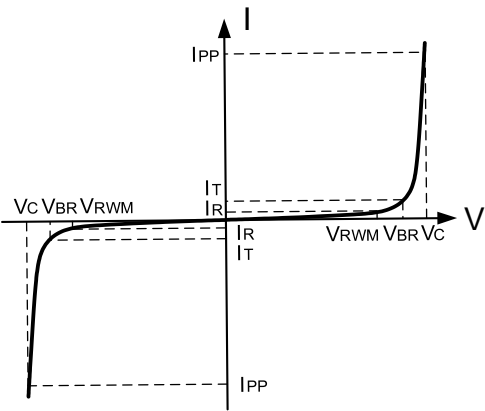
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	60	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	6	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	20 15	kV
Lead Soldering Temperature	T_L	260(10seconds)	$^{\circ}C$
Junction Temperature	T_J	-55 to + 125	$^{\circ}C$
Storage Temperature	T_{stg}	-55 to + 125	$^{\circ}C$

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	3.8			V
Reverse Leakage Current	I_R	$V_{RWM}=3.3\text{V}, T=25^\circ\text{C}$			0.5	μA
Clamping Voltage ²⁾	V_C	$I_{PP}=6\text{A}, t_p=8/20\mu\text{s}$		8		V
Junction Capacitance	C_j	$V_R = 0\text{V}, f = 1\text{MHz}$		12		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

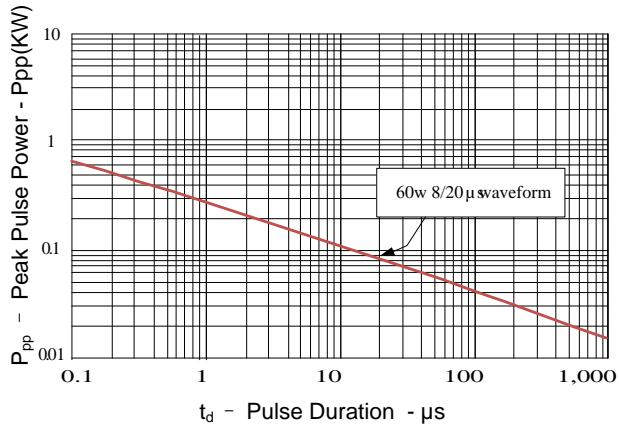


Figure 2: Power Derating Curve

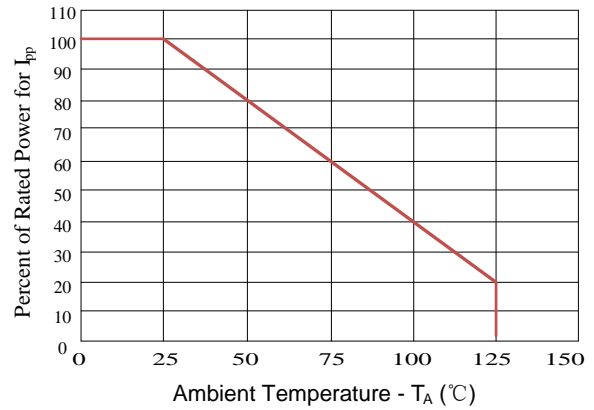


Figure3: Pulse Waveform

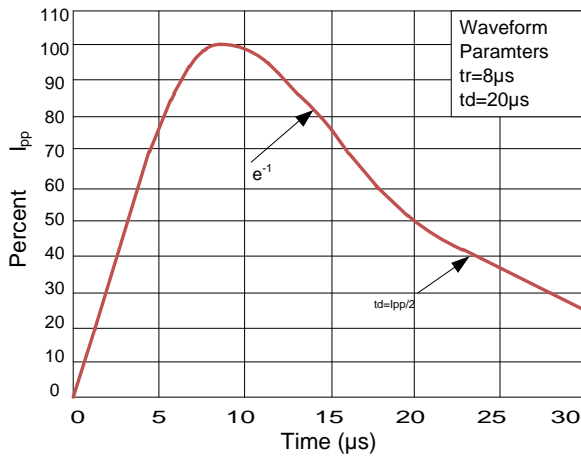
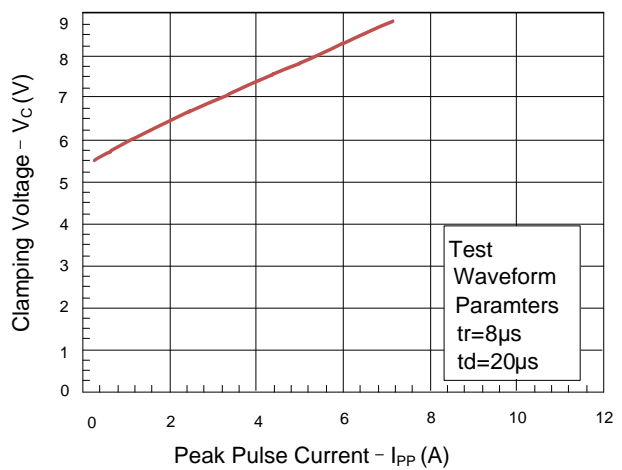
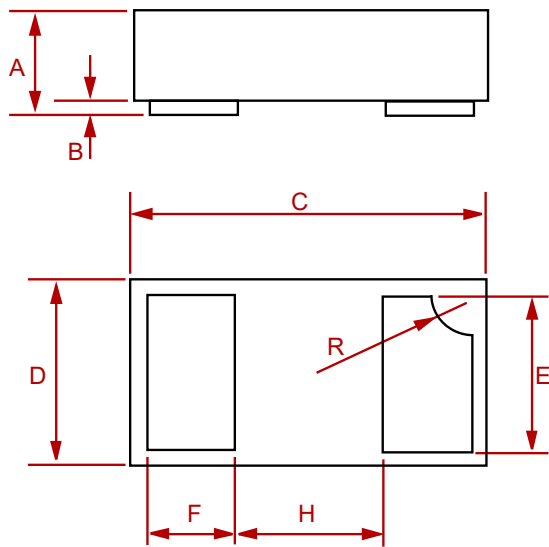


Figure 4: Clamping Voltage vs. Ipp

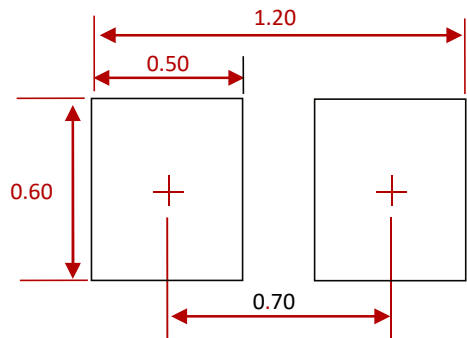


PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.0125	0.02	0.32	0.52
B	0.000	0.002	0.00	0.05
C	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Suggested Pad Layout



- NOTES:
1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR
COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
MSESD8D3.3CAT5G	DFN1006	10000

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